

Supporting Information

Nano-hetero-architectures of two-dimensional (2D) MoS₂@ one-dimensional (1D) brookite TiO₂ nanorods: prominent electron emitters for displays

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(A) Pure 2D MoS₂ layers and 2D MoS₂@1D β -TiO₂ nanorods

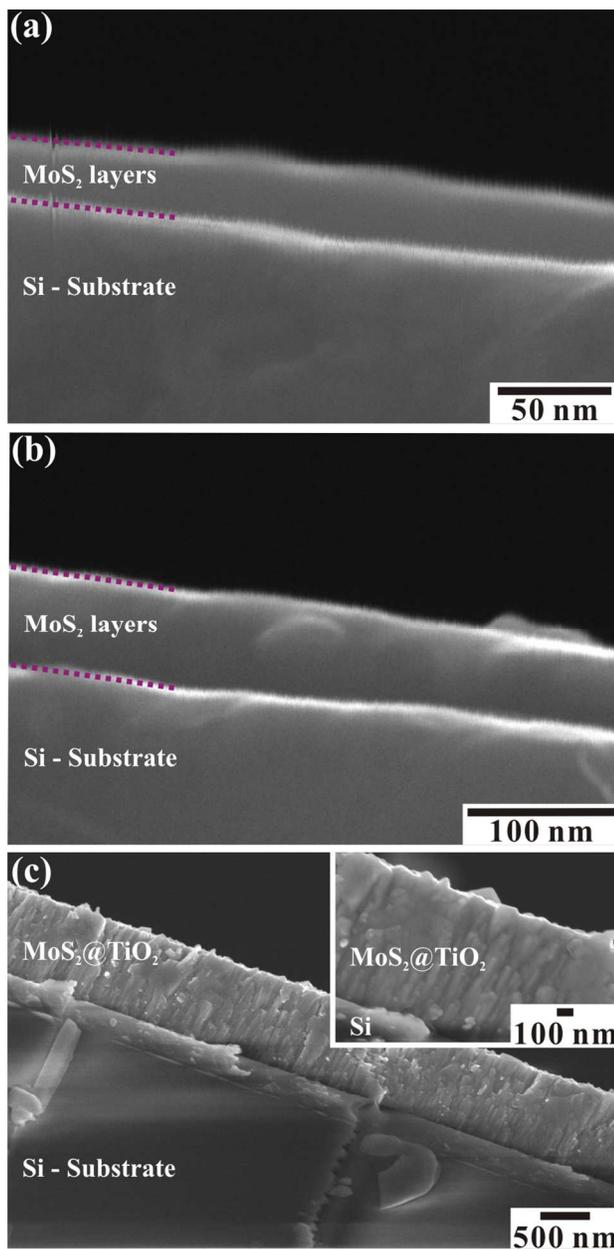


Figure S1. FESEM images showing the cross-sectional view of the large-area array of (a) ~ 20 (± 3) and (b) 40 (± 3) nm thick MoS₂ layers deposited over Si substrate at deposition rate of 500 and 1000 shots, respectively, and (c) 40 (± 3) nm thick MoS₂ layer loaded over 1D β -TiO₂ nanorods. The inset shows the high magnification FESEM image of the portion of 2D MoS₂@1D β -TiO₂ nanorods.

2D MoS₂ layers were deposited over pure Si substrate utilizing PLD technique at optimized conditions. The thickness of MoS₂ was calibrated and confirmed at these optimized conditions before subjected over 1D β -TiO₂ nanorods. High magnification FESEM images in Figure S1 (a and b) shows the cross-sectional views of the MoS₂ thin film produced over Si substrate at deposited rate of \sim 500 and 1000 shots, respectively. The thickness of \sim 40 (\pm 3) nm calibrated at 1000 shots (Figure S1 (b)) was further reduced to the \sim 20 (\pm 3) nm when the deposition was carried out at 500 shots. However, at a deposition rate of 100 shots, the thickness of MoS₂ layer over Si substrate was not clearly distinguishable in FESEM. Therefore, from the calibration of 1000 and 500 shots, it has unanimously been considered that the \sim 4 (\pm 2 nm) nm thick layers of MoS₂ might have produced over Si substrate at the deposition of 100 shots. After these calibrations, 2D MoS₂ layers of \sim 40 (\pm 3), 20 (\pm 3) and 4 (\pm 2) nm were subjected over 1D β -TiO₂ nanorods at their optimized conditions. Figure S1 (c) shows a cross-sectional view of the \sim 40 (\pm 3) nm thick MoS₂ loaded 1D β -TiO₂ nanorods. The 2D MoS₂ layers are formed along the textural boundaries of 1D β -TiO₂ nanorods to fill up the gaps present in between the 1D nanorods (observed in Figure 1(a)). The dense film of 2D MoS₂@1D β -TiO₂ nanorods was observed.

(B) Raman analysis of MoS₂@TiO₂

Raman spectroscopic analysis was employed to study the structural properties of the large area array of 2D MoS₂@1D β -TiO₂ nanorods. Figure S2 shows the Raman spectra for the array of 1D β -TiO₂ nanorods loaded with 40 nm thick layer of 2D MoS₂. There were three Raman bands observed at 218.6, 380.0 and 406.28 cm⁻¹. The existence of the brookite TiO₂ phase is confirmed from the peak observed at 218.6 cm⁻¹, which is assigned to the B_{1g} mode of brookite phase with the space group of D_{2h}^{15} (Pbca) in previous Raman studies of pristine TiO₂ thin films

and nanoparticles.¹⁻³ Furthermore, no peak observed at 513 cm^{-1} assigned to the anatase phase confirm the formation 1D TiO_2 nanorods of pure brookite phase.⁴ The appearance of two prominent peaks at 380 and 406.28 cm^{-1} corresponds to the in-plane E_{2g} and out-of-plane A_{1g} vibration modes, respectively, of the 2D MoS_2 .⁵⁻⁷ The peak frequency difference (Δk) of 26.28 cm^{-1} observed between E_{2g} and A_{1g} confirm the single crystalline multilayer MoS_2 formation over 1D TiO_2 nanorods. These observations are akin to the results for single crystalline monolayer and multilayer of MoS_2 over a sapphire substrate⁶ and MoS_2 multilayers exfoliated with various organolithium compounds.⁷ This confirms that the 40 nm thick layer of 2D has been loaded over 1D TiO_2 nanorods to form nano-hetero-architecture of 2D $\text{MoS}_2@1\text{D } \beta\text{-TiO}_2$ nanorods.

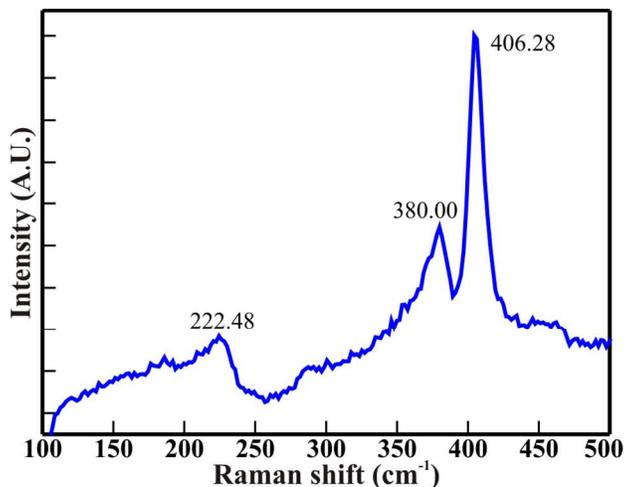


Figure S2. Raman spectrum of the large area array of 2D $\text{MoS}_2@1\text{D } \beta\text{-TiO}_2$ nanorods with 40 nm layer of MoS_2 .

(C) XPS Analysis:

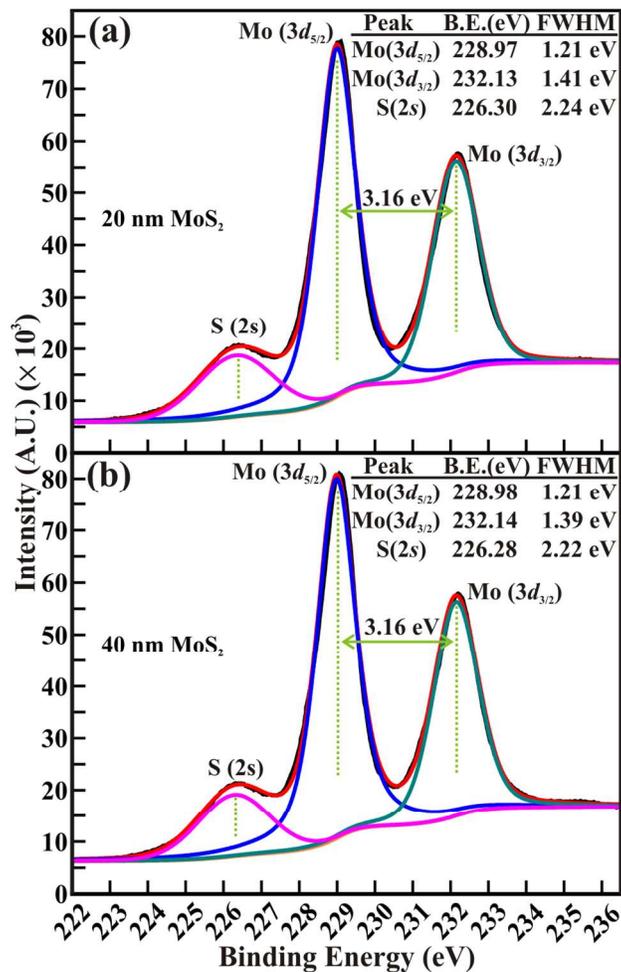


Figure S3. The deconvoluted XPS spectra of Mo ($3d$) core levels of (a) ~ 20 nm and (b) ~ 40 nm thick MoS_2 loaded $\beta\text{-TiO}_2$ nanorods. The XPS spectra are deconvoluted *via* Voigt curve function fitting.

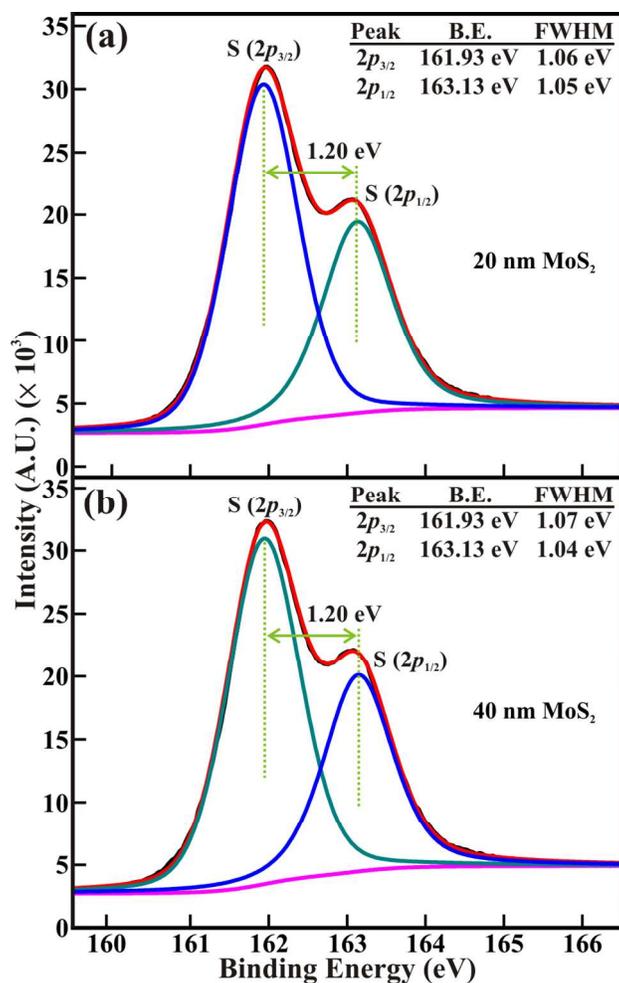


Figure S4. The deconvoluted XPS spectra of S ($2p$) core levels of (a) ~ 20 nm and (b) ~ 40 nm thick MoS_2 loaded $\beta\text{-TiO}_2$ nanorods. The XPS spectra are deconvoluted *via* Voigt curve function fitting.

(D) Field Emission of pure 2D MoS_2 :

FE measurements on 40 nm thick layer of pristine 2D MoS_2 ($\equiv 2\text{D MoS}_2/\text{Si}$) were performed in a planar diode configuration. The macroscopic area of the emitting device was $\sim 0.30 \text{ cm}^2$, and values of the anode-cathode separation used were akin to that of pristine $\beta\text{-TiO}_2$ nanorods i.e. 1000, 1500 and 2000 μm . The variation in the macroscopic electron emission current density (J) as a function of applied electric field (E) shown in Figure S5(a). The emission

current increased rapidly with the gradual increase in applied voltage. The larger emission current density of $\sim 30, 22$ and $19 \mu\text{A}/\text{cm}^2$ was drawn at an applied field of $8.4, 6$ and $4.6 \text{ V}/\mu\text{m}$, respectively with an increasing anode-cathode separation from 1000 to $2000 \mu\text{m}$. Moreover, the turn-on (E_{on}) field required to extract emission current density of $10 \mu\text{A}/\text{cm}^2$ was decreased steadily from 7.2 to $4.3 \text{ V}/\mu\text{m}$ with an increase in the separation from 500 to $2000 \mu\text{m}$. These values of E_{on} are lower than that reported for 3D MoS_2 nanoflowers ($4.5\text{-}5.5 \text{ V}/\mu\text{m}$) synthesized by reducing MoO_2 thin films in the sulfur atmosphere.⁸ Figure S5(b) shows the F-N plot for 2D MoS_2/Si emitter at various separations between anode and cathode. The increase in the separation between cathode and anode commenced for variation in field enhancement factor. The values of β are estimated to be $3905, 4389, 3352,$ and 1476 for the cathode-anode separations of $1000, 1500$ and $2000 \mu\text{m}$, respectively. The viability of the field enhancement factor (β_{FE}) of 2D MoS_2/Si emitters was confirmed from orthodoxy test performed using spreadsheet provided by Forbes. [49*] The scaled-barrier-field (f) values obtained for all cathode-anode separations in 2D MoS_2/Si emitters are shown in Table ST1. The emission situation was found orthodox in all cathode-anode separations for both the lower (f_{low}) and highest (f_{high}) scaled-barrier-field values.

Table ST1: The Scaled-barrier-field (f) values evaluated from F-N plots for $40 (\pm 3 \text{ nm})$ MoS_2/Si emitters obtained using spreadsheet provided in the reference [49]*. Single asterisk on f_{high} values indicates the apparently reasonable values (i.e. $f_{high} < 0.75$).

Separation (μm)	f_{low}	f_{high}	Orthodoxy test result
1000	0.32	0.68	Pass
1500	0.25	0.43	Pass
2000	0.21	0.32	Pass

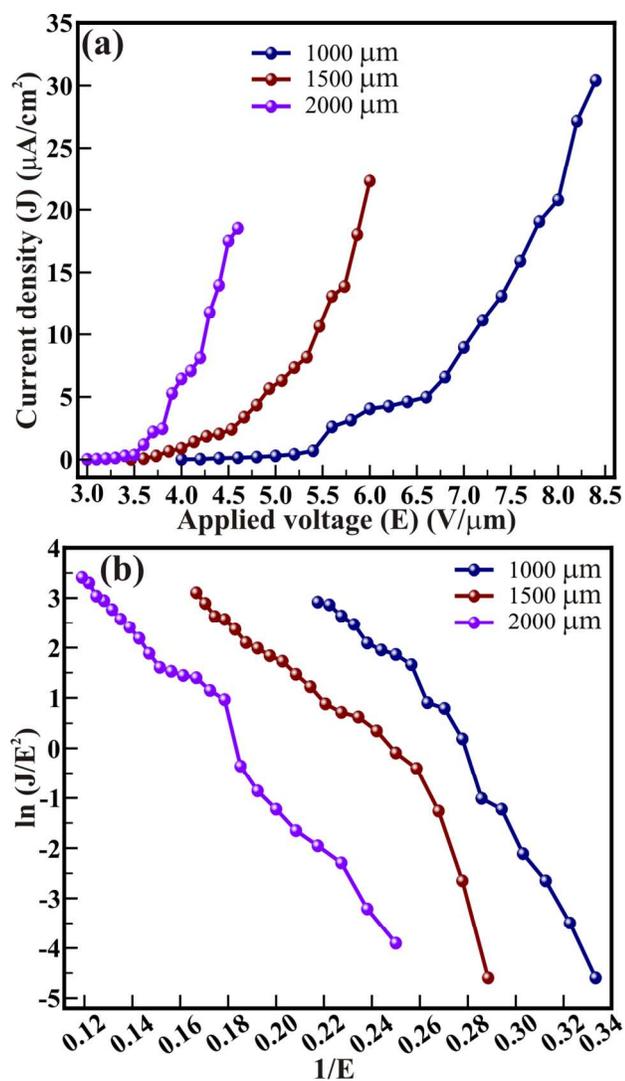


Figure S5. Field emission (a) J-E curves of a large area array of 40 (± 3) nm thick layers of pristine 2D MoS₂ ($\equiv 2\text{D MoS}_2/\text{Si}$) measured at various vacuum separation (i.e. 1000, 1500, and 2000 μm), and their corresponding (b) F-N plots indicating the emission current.

Table ST2. Comparison of the MoS₂/β-TiO₂/Si emitters with the existing Field emitters utilizing pristine metal oxides and their composites.

Sr. No.	Materials	Turn-on field (E_{on})		Threshold field (E_{thr})		Orthodoxy Test	Ref
		Observed	Defined	Observed	Defined		
		V/ μ m	μ A/cm ²	V/ μ m	μ A/cm ²		
1.	2D MoS ₂ @1D β -TiO ₂ nanorods	2.5	10	3.6	100	Pass	
2.	MoS ₂ protrusions	2.8	10	-	-	Not performed	^{48*}
3.	MoS ₂ sheets	3.5	10	-	-	Not performed	^{19*}
4.	C doped TiO ₂ nanotubes	5.0	10	-	-	Not performed	^{14*}
5.	Fe doped TiO ₂ nanotubes	12	10			Not performed	^{13*}
6.	3.88 % N doped TiO ₂ nanotubes	10	> 33	11.76	1000	Not performed	^{6*}
7.	4.12 % N doped TiO ₂ nanotubes	9.21	> 33	14.61	1000	Not performed	^{6*}
8.	4.74 % N doped TiO ₂ nanotubes	6.54	> 33	20.43	1000	Not performed	^{6*}
9.	TiO ₂ -based TiO ₂ @MoS ₂ composites (flower like spheres)	3.1 - 2.5	01	7.2 - 4.5	100	Not performed	^{23*}
10.	MoS ₂ -based MoS ₂ @TiO ₂ composites (hierarchical spheres)	4 - 2.2	01	6.1 - 3.6	100	Not performed	^{23*}
11.	TiO ₂ nanorods	14	10	20	100	Not performed	^{24*}
12.	MoS ₂ @TiO ₂ nanorods heterostructure	11	10	17	100	Not performed	^{24*}
13.	MoS ₂ nanoflowers	3.65	10	9.03	1000	Not performed	^{20*}
14.	MoS ₂ @ZnO heterojunctions	3.08	10	6.9	1000	Not performed	^{20*}
15.	MoS ₂ nanoflowers	4.2	01	6.2	100	Not performed	^{21*}
16.	MoS ₂ @SnO ₂ hetero-nanoflowers	3.4	01	5.2	100	Not performed	^{21*}

* References are cited in the main text of the manuscript

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